74LVC1G38

2-input NAND gate; open drain Rev. 7 — 4 October 2012

Product data sheet

1. **General description**

The 74LVC1G38 provides a 2-input NAND function.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device as translator in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V).
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- \pm 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Open drain outputs
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from –40 °C to +125 °C.



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3. Ordering information

Table 1. Ordering information

Type number	Package							
	Temperature range Name		Description	Version				
74LVC1G38GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1				
74LVC1G38GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753				
74LVC1G38GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886				
74LVC1G38GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891				
74LVC1G38GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115				
74LVC1G38GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202				
74LVC1G38GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226				

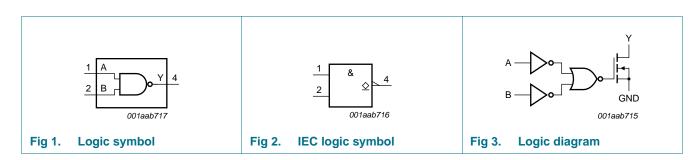
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74LVC1G38GW	YB
74LVC1G38GV	YB
74LVC1G38GM	YB
74LVC1G38GF	YB
74LVC1G38GN	YB
74LVC1G38GS	YB
74LVC1G38GX	YB

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



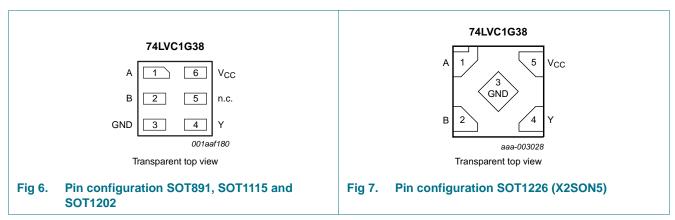
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6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin	Pin			
	TSSOP5 and X2SON5	XSON6			
Α	1	1	data input		
В	2	2	data input		
GND	3	3	ground (0 V)		
Υ	4	4	data output		
n.c.	-	5	not connected		
V _{CC}	5	6	supply voltage		

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7. Functional description

Table 4. Function table[1]

Input		Output
Α	В	Υ
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

^[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF state

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		, ,			,
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V _I	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0 V$	-	±50	mA
V _O	output voltage	Active mode	<u>[1][2]</u> –0.5	+6.5	V
		Power-down mode	<u>[1][2]</u> –0.5	+6.5	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[3]</u> _	300	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] When $V_{CC} = 0 \text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

^[3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 and X2SON 5packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	Active mode	0	-	5.5	V
		Disable mode; $V_{CC} = 1.65 \text{ V}$ to 5.5 V	0	-	5.5	V
		Power-down mode; V _{CC} = 0 V	0	-	5.5	V
T _{amb}	ambient temperature		-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C[1]					
V_{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3 \times V_{\text{CC}}$	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}	-	-	-	
		$I_O = 100 \ \mu A; \ V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	-	-	0.1	V
		$I_O = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.3	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	V
l _l	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±5	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	±0.1	±10	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 5.5 \text{ V}$; $V_{CC} = 0 \text{ V}$	-	±0.1	±10	μΑ
I _{CC}	supply current	V _I = 5.5 V or GND; V _{CC} = 1.65 V to 5.5 V; I _O = 0 A	-	0.1	10	μΑ
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V} \text{ to } 5.5 \text{ V}; \text{ per pin}$	-	5	500	μΑ
C _I	input capacitance		-	2.5	-	pF

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 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}	-	-	-	
		I_O = 100 $\mu A;V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	٧
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	٧
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		$I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V
l _l	input leakage current	$V_1 = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	±100	μΑ
loz	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±200	μА
OFF	power-off leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	-	±200	μΑ
lcc	supply current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$	-	-	200	μА
Δl _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V} \text{ to } 5.5 \text{ V}; \text{ per pin}$	-	-	5000	μА

^[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

2-input NAND gate; open drain

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 9.

Symbol	Parameter	Conditions		-40 °C to +85 °C			-40 °C to	-40 °C to +125 °C	
				Min	Typ[1]	Max	Min	Max	
t _{pd}	propagation delay	A, B to Y; see Figure 8	[2]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.0	3.0	10.0	1.0	12.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.5	1.8	6.0	0.5	7.5	ns
		$V_{CC} = 2.7 V$		0.5	2.5	5.0	0.5	6.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.5	2.3	4.5	0.5	5.7	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	1.5	3.9	0.5	4.9	ns
C_{PD}	power dissipation capacitance	$V_{CC} = 3.3 \text{ V};$ $V_I = \text{GND to } V_{CC}$	[3]	-	6	-	-	-	pF

^[1] Typical values are measured at $T_{amb} = 25$ °C and $V_{CC} = 1.8$ V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

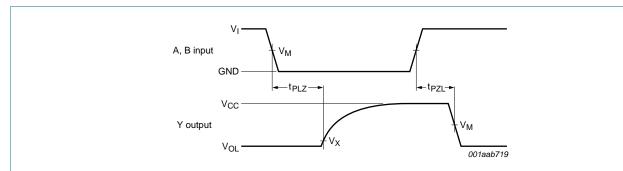
C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = sum of outputs.$

12. AC waveforms



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

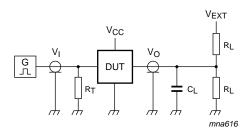
Fig 8. The input (A, B) to output (Y) propagation delays.

^[2] t_{pd} is the same as t_{PZL} and t_{PLZ} .

2-input NAND gate; open drain

Table 9. Measurement points

Supply voltage	Input	Output	
V _{CC}	V _M	V _M	V _X
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V
2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V
3.0 V to 3.6 V	1.5 V	1.5 V	V _{OL} + 0.3 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.3 V



Test data is given in Table 10.

Definitions for test circuit:

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

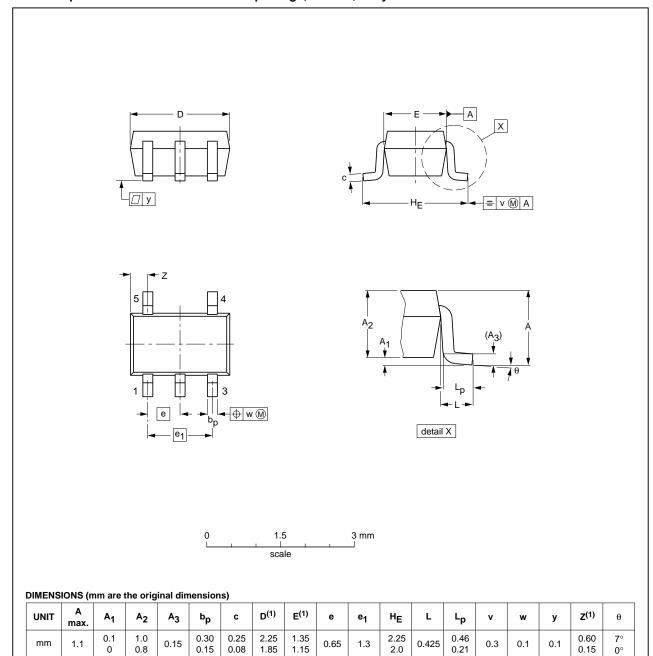
Supply voltage	Input		Load		V _{EXT}
V _{CC}	VI	t _r , t _f	CL	R _L	t _{PLH} , t _{PHL}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open

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13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT353-1		MO-203	SC-88A			-00-09-01- 03-02-19

Fig 10. Package outline SOT353-1 (TSSOP5)

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Plastic surface-mounted package; 5 leads

SOT753

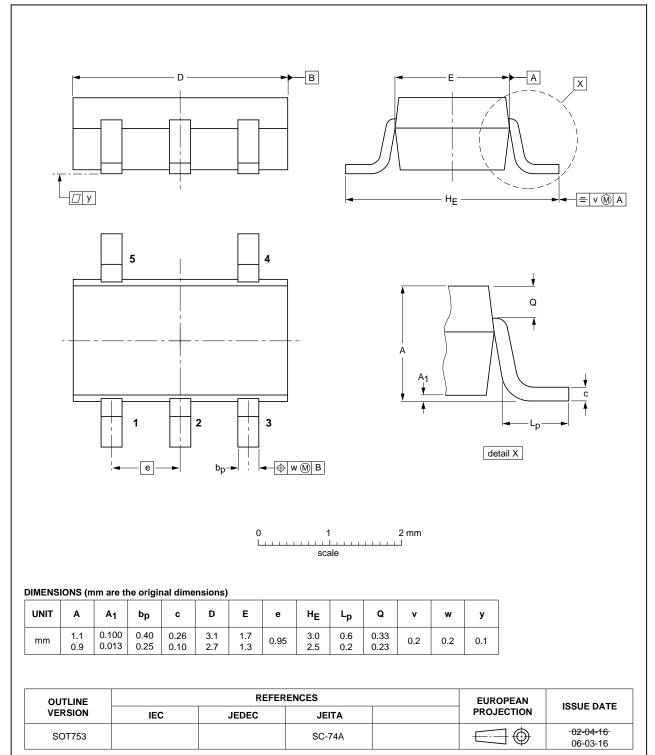


Fig 11. Package outline SOT753 (SC-74A)

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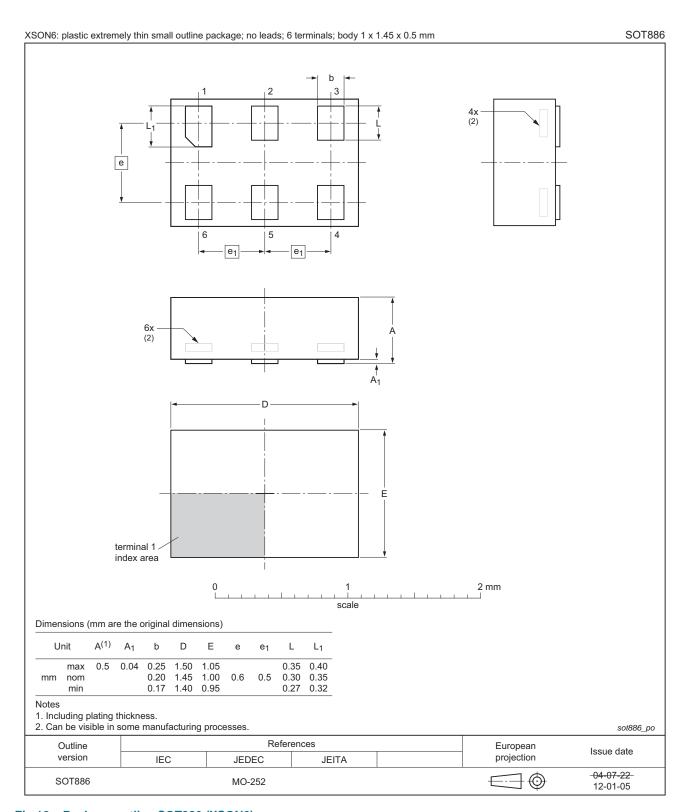


Fig 12. Package outline SOT886 (XSON6)

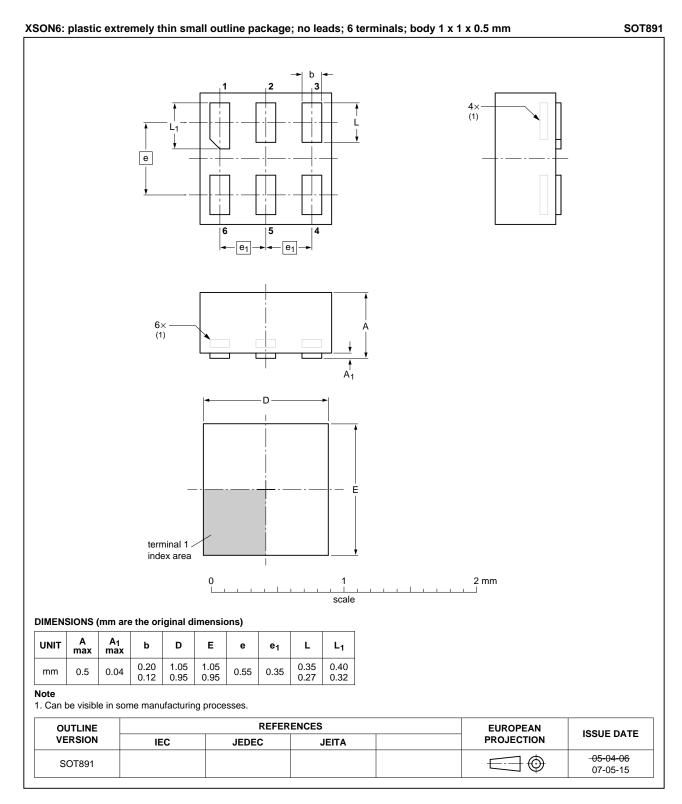


Fig 13. Package outline SOT891 (XSON6)

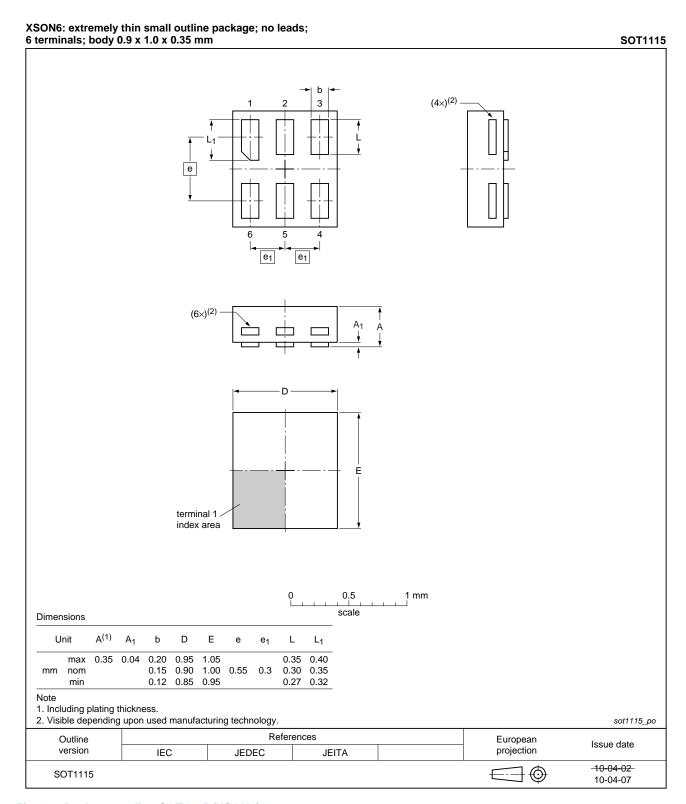


Fig 14. Package outline SOT1115 (XSON6)

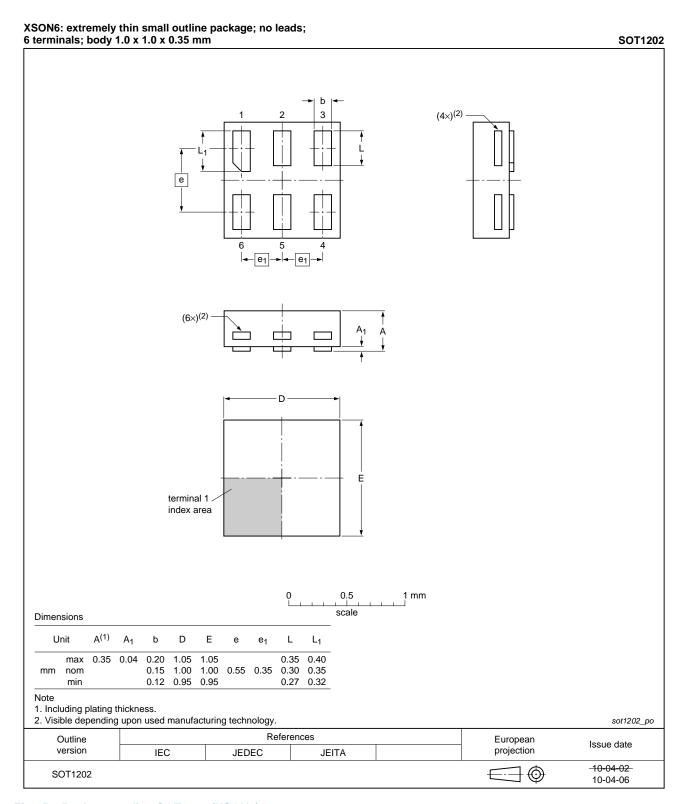


Fig 15. Package outline SOT1202 (XSON6)

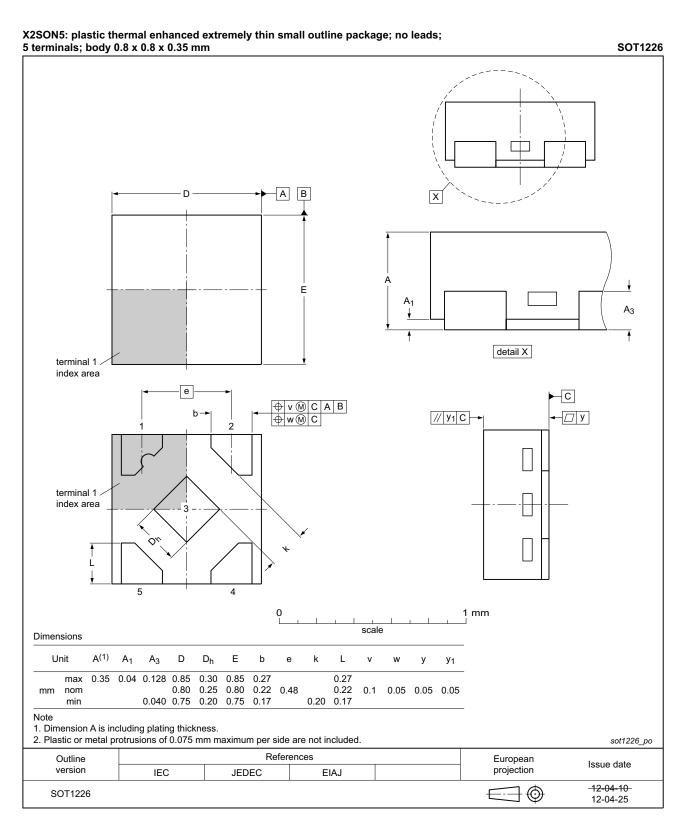


Fig 16. Package outline SOT1226 (X2SON5)

2-input NAND gate; open drain

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G38 v.7	20121004	Product data sheet	-	74LVC1G38 v.6
Modifications:	• Pin configuration SOT1226 (Figure 7) modified.			
74LVC1G38 v.6	20120702	Product data sheet	-	74LVC1G38 v.5
Modifications:	 Added type num 	ber 74LVC1G38GX (SOT1226)		
	 Package outline 	drawing of SOT886 (Figure 12) mo	odified.	
74LVC1G38 v.5	20111206	Product data sheet	-	74LVC1G38 v.4
Modifications:	ns: • Legal pages updated.			
74LVC1G38 v.4	20101005	Product data sheet	-	74LVC1G38 v.3
74LVC1G38 v.3	20070827	Product data sheet	-	74LVC1G38 v.2
74LVC1G38 v.2	20060913	Product data sheet	-	74LVC1G38 v.1
74LVC1G38 v.1	20041018	Product data sheet	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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